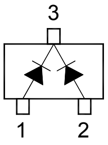
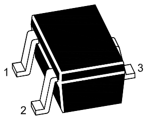
1SS301CCW

Silicon Epitaxial Planar Switching Diode





SOT-323 Plastic Package
Marking Code: **PH**

Applications

- Ultra high speed switching

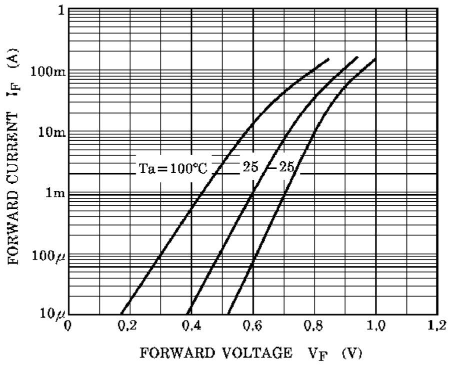
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	I_{FM}	300	mA
Non-repetitive Peak Forward Surge Current (tp = 10 ms)	I_{FSM}	2	A
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

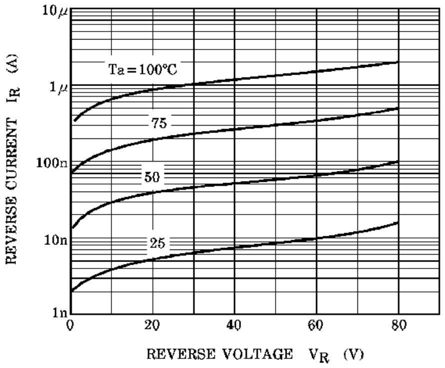
Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	-	1.2	V
Reverse Current at V_R = 30 V at V_R = 80 V	I_R	- -	0.1 0.5	µA
Total Capacitance at V_R = 0, f = 1 MHz	C_T	-	3	pF
Reverse Recovery Time at I_F = 10 mA, V_R = 6 V, I_{rr} = 1 mA, R_L = 100 Ω	t_{rr}	-	4	ns

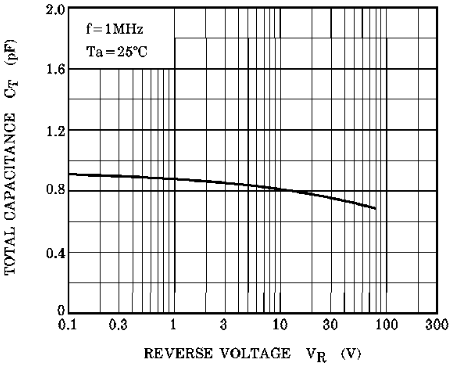
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



$t_{rr} - I_F$